



INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known			
		Application Number	10/822,345		
		Filing Date	April 12, 2004		
		First Named Inventor	Meng Tao		
		Group Art Unit	2842 2813		
		Examiner Name	Not Yet Assigned Colleen E. Rodgers		
Sheet	1	of	2	Attorney Docket Number	124263-1019

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
CR		R.M. TROMP, R.J. HAMERS, and J.E. DEMUTH, Si(001) ^{dimer} dimmer structure observed with scanning tunneling microscopy, Phys. Rev. Lett., 1985, 1303, 55	
CR		E. KAXIRAS, Semiconductor-surface restoration by valence-mending absorbates: Application to Si(100):S and Si(100):Se, Physical Review B, 1991, 6324, 43	
CR		H. METZNER, TH. HALN, and J.-H. BREMER, Structure of sulfur-terminated silicon surfaces, Surf. Sci., 1997, 377-371-374, 379,	
CR		J.J. BOLAND, Structure of the H-saturated Si(100) surface, Phys. Rev. Lett., 1990, 3325, 65	
CR		M. TAO and L.P. HUNT, The thermodynamic behavior of the Si-H system and its role in Si-CVD from SiH ₄ , J. Electrochem. Soc., 1992, 806, 139	
CR		J.E. NORTHRUP, Structure of Si(100)H: Dependence on the H chemical potential, Phys. Rev. B, 1991, 1419, 44	
CR		B.S. MEYERSON, F.J. HIMPSEL, and K. J. URAM, Bistable conditions for low-temperature silicon epitaxy, Appl. Phys. Lett., 1990, 1034, 57	
CR		J.W. LYDING, T.-C SHEN, J.S. HUBACEK, J.R. TUCKER, and G.C. ABELN, Nanoscale patterning and oxidation of H-passivated Si(100)-2x1 surfaces with an ultrahigh vacuum scanning tunneling microscope, Appl. Phys. Lett., 1994, 2010, 64	
CR		T.-C SHEN, C. WANG, G.C. ABELN, J.R. TUCKER, J.W. LYDING, PH. AVOURIS, and R.E. WALKUP, Atomic-scale desorption through electronic and vibrational excitation mechanisms, Science, 1995, 1590, 268	
CR		J.W. LYDING, UHV STM nanofabrication: progress, technology spin-offs, and challenges, Proceedings of the IEEE, 1997, 589, 85	
CR		T.-C. SHEN, C. WANG, and J.R. TUCKER, Al nucleation on monohydride and bare Si (001) surfaces: atomic scale patterning, Phys. Rev. Lett., 1997, 1271, 78	

Examiner Signature	Colleen E. Rodgers	Date Considered	06/18/06
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			Application Number	10/822,345	
			Filing Date	April 12, 2004	
			First Named Inventor	Meng Tao	
			Group Art Unit	2812	
			Examiner Name	Not Yet Assigned	
Sheet	2	of	2	Attorney Docket Number	124283-1019

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
Examiner's Initials No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
CR	I. LYUBINETSKY, Z. DOHNALEK, W.J. CHOYKE, and J.T. YATES, JR., Cl ₂ dissociation on Si(100)-(2x1): A statistical study by scanning tunneling microscopy, Phys. Rev. B, 1998, 7950, 58	
CR	M. CHANDER, Y.Z. LI, D. RIOUX, and J.H. WEAVER, Patterning of Si(100): Spontaneous etching with Br ₂ , Phys. Rev. Lett., 1993, 4154, 71	
CR	The National Technology Roadmap for Semiconductors, Semiconductor Industry Association, 1997	
CR	A. M. COWLEY, S. M. SZE, Surface States and Barrier Height of Metal-Semiconductor Systems, J. Appl. Phys, 1965, 3212-3220, 36	
CR	J. P. LACHARME, N. BENAZZI, C. A. SEBENNE, Compositional and electronic properties of Si(001)2X1 upon diatomic sulfur interaction, Surf. Sci., 1999, 415-419, 433-435	
CR	A. C. PAPAGEORGIOPOULOS, M. KAMARATOS, Adsorption and desorption of Se on Si(100)2X1: surface restoration, Surf. Sci., 1999, 415-419, 433-435	
CR	MICHAELSON, HERBERT B., The work function of the elements and its periodicity, J. Appl. Phys., 1977, 4729-33, 48	

Examiner Signature	<i>Colleen E. DeF...</i>	Date Considered	06/18/06
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Sheet 1 of 1

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Filing Date	April 12, 2004
First Named Inventor	Meng TAO
Art Unit	2813
Examiner Name	Unknown Colleen E. Rodgers
Attorney Docket Number	124263-1019

U. S. PATENT DOCUMENTS

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FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

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